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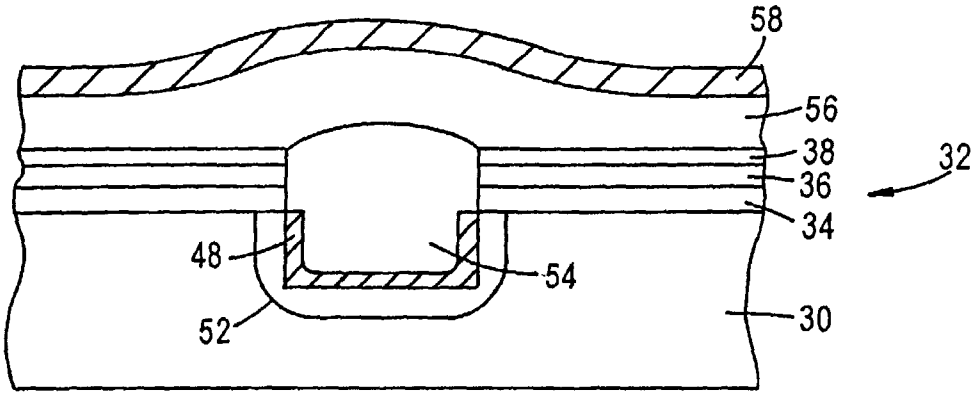
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(54) Title: MONOS DEVICE HAVING BURIED METAL SILICIDE BIT LINE



(57) Abstract: A MONOS device and method for making the device has a charge trapping dielectric layer (32), such as an oxide-nitride-oxide (ONO) layer (34, 36, 38), formed on a substrate (30). A recess (44) is created through the ONO layer (32) and in the substrate (30). A metal silicide bit line (48) is formed in the recess (44) and bit line oxide (54) is formed on top of the metal silicide. A word line (56) is formed over the ONO layer (32) and the bit line oxide (54), and a low resistance silicide (58) is provided on top of the word line (56). The silicide (58) is formed by laser thermal annealing, for example.

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